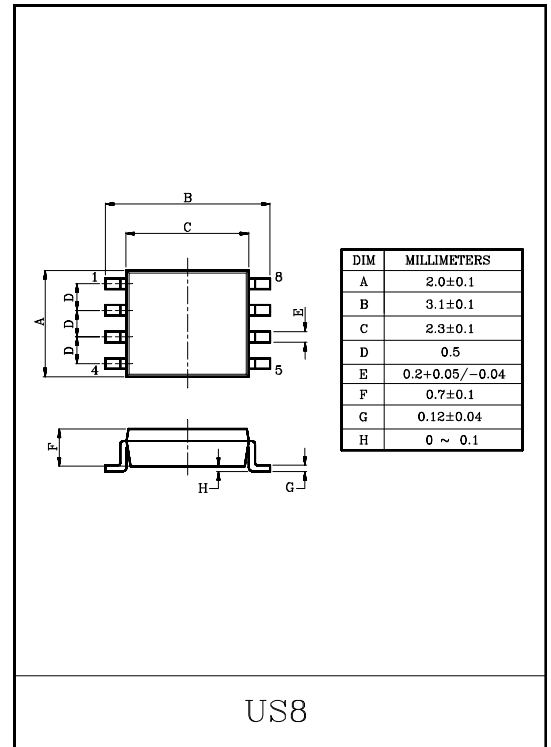


DUAL BILATERAL SWITCH

The KIC7W66FK is a high speed C²MOS DUAL BILATERAL SWITCH fabricated with silicon gate C²MOS technology. It consists of four independent high speed switches capable of controlling either digital or analog signals while maintaining the CMOS low power dissipation. Control input (C) is provided to control the switch. The switch turns ON while the C input is high, and the switch turns OFF while low. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES

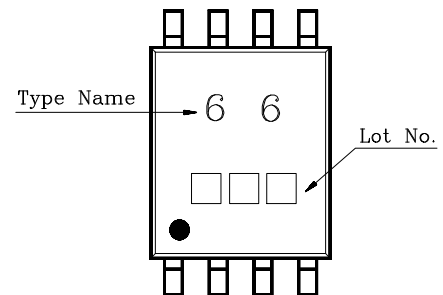
- High Speed : $t_{pd}=7\text{ns}(\text{Typ.})$ at $V_{CC}=5\text{V}$.
- Low Power Dissipation : $I_{CC}=1\mu\text{A}(\text{Max.})$ at $T_a=25^\circ\text{C}$.
- High Noise Immunity : $V_{NIH}=V_{NIL}=28\% V_{CC}(\text{Min.})$.
- Low ON Resistance : $R_{ON}=50\Omega(\text{Typ.})$ at $V_{CC}=9\text{V}$
- High Degree of Linearity : $\text{THD}=0.05(\text{Typ.})$ at $V_{CC}=5\text{V}$



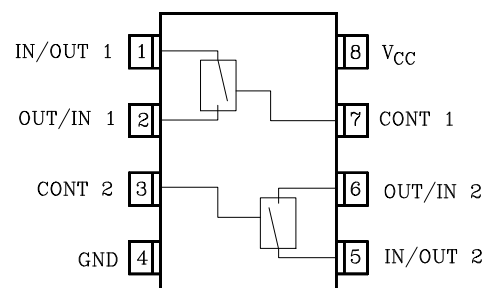
MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	-0.5~10	V
Control Input Voltage	V_{IN}	-0.5~ $V_{CC}+0.5$	V
Switch I/O Voltage	V_{IO}	-0.5~ $V_{CC}+0.5$	V
Control Input Diode Current	I_{CK}	±20	mA
I/O Diode Current	I_{IOK}	±20	mA
Switch Through Current	I_T	±25	mA
DC V_{CC} /Ground Current	I_{CC}	±50	mA
Power Dissipation	P_D	200	mW
Storage Temperature	T_{stg}	-65~150	°C
Lead Temperature (10s)	T_L	260	°C

MARKING

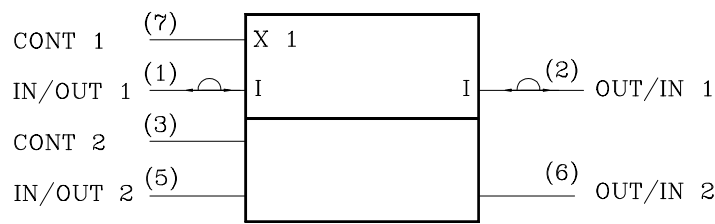


PIN CONNECTION(TOP VIEW)



KIC7W66FK

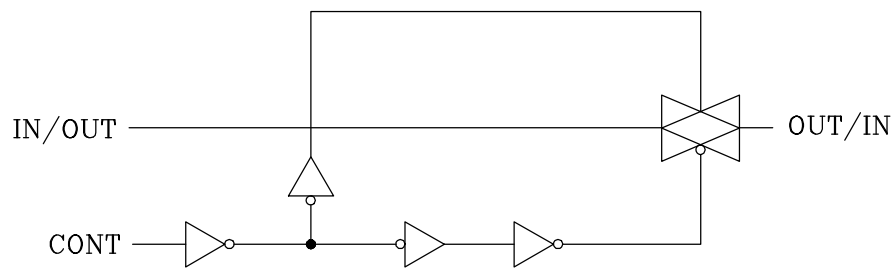
LOGIC SYMBOL



TRUTH TABLE

CONTROL	SWITCH FUNCTION
H	ON
L	OFF

LOGIC DIAGRAM



RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2~9	V
Control Input Voltage	V_{IN}	0~ V_{CC}	V
Switch I/O Voltage	$V_{I/O}$	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	t_r, t_f	0~1000 ($V_{CC}=2.0V$) 0~ 500 ($V_{CC}=4.5V$) 0~ 400 ($V_{CC}=6.0V$) 0~ 250 ($V_{CC}=9.0V$)	ns

KIC7W66FK

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{CC}	Ta=25℃			Ta=-40~85℃		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High-Level Control Input Voltage	V _{IHC}		2.0 4.5 9.0	1.5 3.15 6.3	- - -	- - -	1.5 3.15 6.3	- - -	V
Low-Level Control Input Voltage	V _{ILC}		2.0 4.5 9.0	- - -	- - -	0.5 1.35 2.7	- - -	0.5 1.35 2.7	V
ON Resistance	R _{ON}	V _{IN} =V _{IHC} V _{I/O} =V _{CC} or GND I _{I/O} ≤1mA	4.5 9.0	- -	96 55	170 85	- -	200 100	Ω
		V _{IN} =V _{IHC} V _{I/O} =V _{CC} or GND I _{I/O} ≤1mA	2.0 4.5 9.0	- - -	160 70 50	- 100 75	- - -	- 130 95	
Difference of ON Resistance Between Switches	ΔR _{ON}	V _{IN} =V _{IHC} V _{I/O} =V _{CC} to GND I _{I/O} ≤1mA	4.5 9.0	- -	10 5	- -	- -	- -	Ω
Input/Output Leakage Current (SWITCH OFF)	I _{OFF}	V _{OS} =V _{CC} or GND V _{I/S} =GND or V _{CC} V _{IN} =V _{ILC}	9.0	-	-	±100	-	±1000	nA
Switch Input Leakage Current (SWITCH ON OUTPUT OPEN)	I _{IZ}	V _{OS} =V _{CC} or GND V _{INH} =V _{IHC}	9.0	-	-	±100	-	±1000	nA
Control Input Current	I _{IN}	V _{IN} =V _{CC} or GND	6.0	-	-	±100	-	±1000	nA
Quiescent Supply Current	I _{CC}	V _{IN} =V _{CC} or GND	6.0 9.0	- -	- -	1.0 4.0	- -	10.0 40.0	μA

KIC7W66FK

AC ELECTRICAL CHARACTERISTICS (C_L=50pF, Input, t_r=t_f=6ns)

CHARACTERISTIC	SYMBOL	TEST CONDITION		Ta=25℃			Ta=-40～85℃		UNIT
			V _{CC}	MIN.	TYP.	MAX.	MIN.	MAX.	
Phase Difference Between Input and Output	ϕ I/O		2.0 4.5 9.0	- - -	10 4 3	50 10 8	- - -	65 13 10	ns
Output Enable Time	t _{pZL} t _{pZH}	R _L =1kΩ	2.0 4.5 9.0	- - -	18 8 6	100 20 12	- - -	125 25 22	ns
Output Disable Time	t _{pLZ} t _{pHZ}	R _L =1kΩ	2.0 4.5 9.0	- - -	20 10 8	115 23 20	- - -	145 29 25	ns
Maximum Control Input Frequency		R _L =1kΩ CL=15pF V _{OUT} =1/2V _{CC}	2.0 4.5 9.0	- - -	30 30 30	- - -	- - -	- - -	MHz
Control Input Capacitance	C _{IN}			-	5	10	-	10	pF
Switch Terminal Capacitance	C _{I/O}			-	6	-	-	-	pF
Feed Through Capacitance	C _{IOS}			-	0.5	-	-	-	pF
Power Dissipation Capacitance	C _{PD}	(Note 1)		-	15	-	-	-	pF

Note 1 : C_{PD} is defined as the value of internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

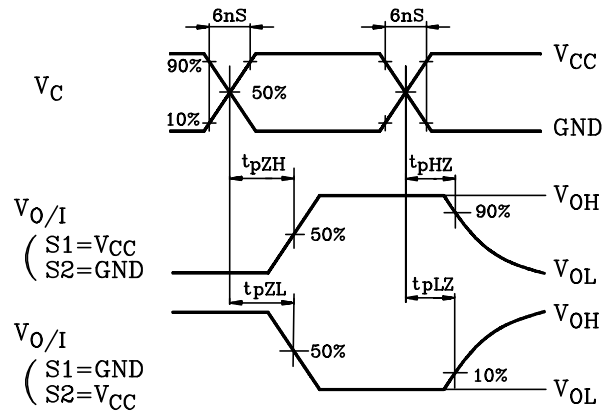
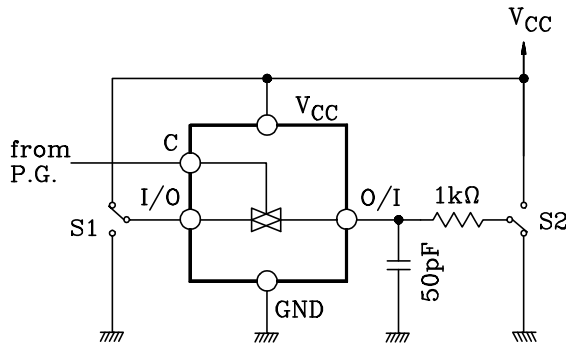
$$I_{CC(oper)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2$$

ANALOG SWITCH CHARACTERISTICS (GND=0V, Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{CC}	TYP.	UNIT
Sine Wave Distortion (T.H.D)		f _{IN} =1kHz, V _{IN} =4.0V _{P-P} @V _{CC} =4.5V R _L =10kΩ, V _{IN} =8.0V _{P-P} @V _{CC} =9.0V C _L =50pF	4.5	0.05	%
			9.0	0.04	
Frequency Response (Switch ON)	f _{MAX}	Adjust f _{IN} voltage to obtain 0dBm at V _{OS} Increase f _{IN} Frequency until dB Meter reads -3dB R _L =50Ω, C _L =10pF, f _{IN} =1MHz, Sine Wave	4.5	200	MHz
			9.0	200	
Feedthrough Attenuation (Switch OFF)		Vin is centered at V _{CC} /2 Adjust input for 0dBm R _L =600Ω, C _L =50pF, f _{IN} =1MHz, Sine Wave	4.5	-60	dB
			9.0	-60	
Crosstalk (Control Input to Signal Output)		R _L =600Ω, C _L =50pF, f _{IN} =1MHz, Square Wave (t _r =t _f =6ns)	4.5	60	mV
			9.0	100	
Crosstalk (Between any switches)		Adjust V _{IN} to obtain 0dBm at Input R _L =600Ω, C _L =50pF, f _{IN} =1MHz, Sine Wave	4.5	-60	dB
			9.0	-60	

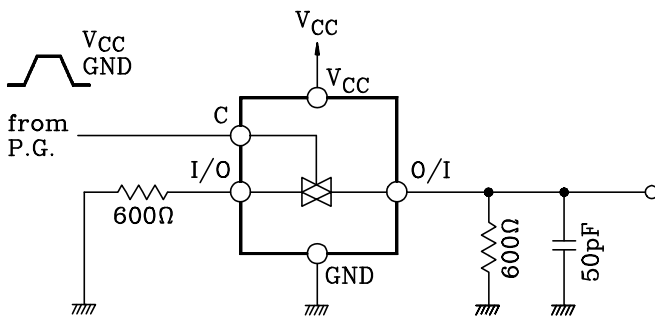
SWITCHING CHARACTERISTICS TEST CIRCUITS

1. t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

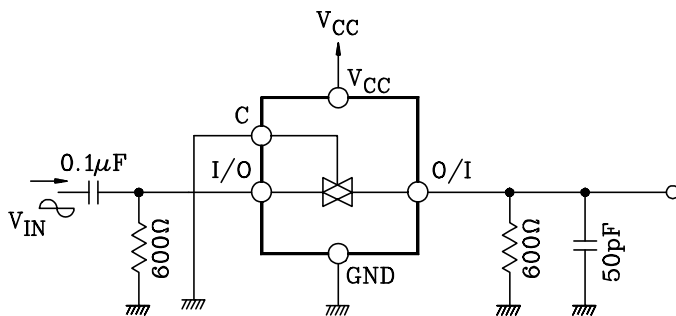


2. CROSS TALK (CONTROL INPUT-SWITCH OUTPUT)

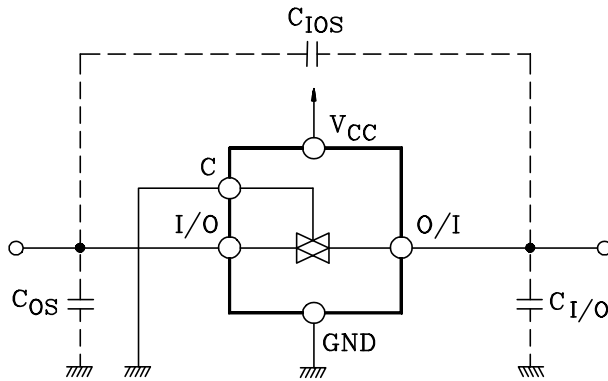
$f_{IN}=1\text{MHz}$, duty=50%, $t_r=t_f=6\text{ns}$



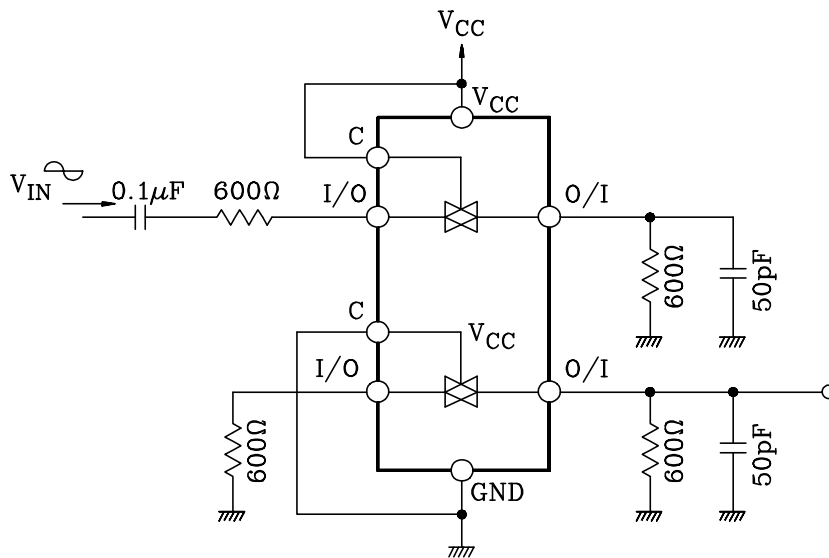
3. FEEDTHROUGH ATTENUATION



4. C_{IOS} , $C_{I/O}$



5. CROSS TALK (BETWEEN ANY TWO SWITCHES)



3. FREQUENCY RESPONSE (SWITCH ON)

